

SEMICONDUCTOR

TECHNICAL DATA

2SC9012

EPITAXIAL PLANAR PNP TRANSISTOR

GENERAL PURPOSE APPLICATION.
SWITCHING APPLICATION.

FEATURES

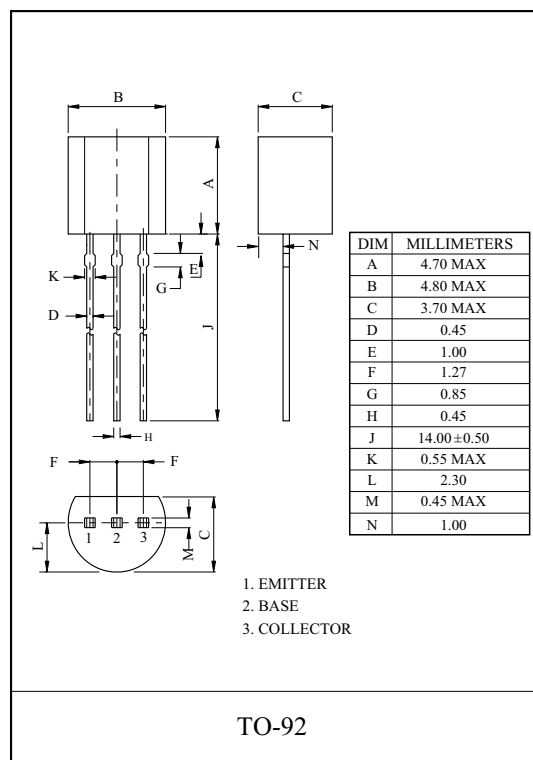
- Excellent h_{FE} Linearity.
- Complementary to KTC9013.

MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-500	mA
Emitter Current	I_E	500	mA
Collector Power Dissipation	P_C^*	625	mW
		400	
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55 150	°C

* Cu Lead-Frame : 625mW

Fe Lead-Frame : 400mW



ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=-35V, I_E=0$	-	-	-0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=-5V, I_C=0$	-	-	-0.1	μA
DC Current Gain	h_{FE} (Note)	$V_{CE}=-1V, I_C=-50mA$	64	-	246	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-100mA, I_B=-10mA$	-	-0.1	-0.25	V
Base-Emitter Voltage	V_{BE}	$I_C=-100mA, V_{CE}=-1V$		-0.8	-1.0	V
Transition Frequency	f_T	$V_{CB}=-6V, I_C=-20mA, f=100MHz$	150	-	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-6V, I_E=0, f=1MHz$	-	7.0	-	pF

Note : h_{FE} Classification D:64 91, E:78 112, F:96 135, G:118 166, H:144 202, I:176 246

